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Understanding Embedded - Microprocessors

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of **Embedded - Microprocessors**

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details

Obsolete
PowerPC e300c3
1 Core, 32-Bit
266MHz
-
DDR2
No
-
10/100/1000Mbps (3)
-
USB 2.0 (1)
1.8V, 2.5V, 3.3V
-40°C ~ 105°C (TA)
-
473-LFBGA
473-MAPBGA (19x19)
https://www.e-xfl.com/product-detail/nxp-semiconductors/mpc8308czqadd

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1 Overview

This figure shows the major functional units within the MPC8308. The e300 core in the MPC8308, with its 16 Kbytes of instruction and 16 Kbytes of data cache, implements the Power Architecture user instruction set architecture and provides hardware and software debugging support. In addition, the MPC8308 offers a PCI Express controller, two three-speed 10, 100, 1000 Mbps Ethernet controllers (eTSEC), a DDR2 SDRAM memory controller, a SerDes block, an enhanced local bus controller (eLBC), an integrated programmable interrupt controller (IPIC), a general purpose DMA controller, two I²C controllers, dual UART (DUART), GPIOs, USB, general purpose timers, and an SPI controller. The high level of integration in the MPC8308 helps simplify board design and offers significant bandwidth and performance.

This figure shows a block diagram of the device.



Figure 1. MPC8308 Block Diagram

2 Electrical Characteristics

This section provides the AC and DC electrical specifications and thermal characteristics for the MPC8308. The device is currently targeted to these specifications. Some of these specifications are independent of the I/O cell, but are included for a more complete reference. These are not purely I/O buffer design specifications.

2.1 Overall DC Electrical Characteristics

This section covers the ratings, conditions, and other characteristics.

6 DDR2 SDRAM

This section describes the DC and AC electrical specifications for the DDR2 SDRAM interface. Note that DDR2 SDRAM is $GV_{DD}(typ) = 1.8 V$.

6.1 DDR2 SDRAM DC Electrical Characteristics

This table provides the recommended operating conditions for the DDR2 SDRAM component(s) when $GV_{DD}(typ) = 1.8 \text{ V}.$

Parameter/Condition	Symbol	Min	Мах	Unit	Note
I/O supply voltage	GV _{DD}	1.7	1.9	V	1
I/O reference voltage	MV _{REF}	$0.49 imes GV_{DD}$	$0.51 \times GV_{DD}$	V	2
I/O termination voltage	V _{TT}	MV _{REF} - 0.04	MV _{REF} + 0.04	V	3
Input high voltage	V _{IH}	MV _{REF} + 0.125	GV _{DD} + 0.3	V	_
Input low voltage	V _{IL}	-0.3	MV _{REF} – 0.125	V	_
Output leakage current	I _{OZ}	-9.9	9.9	μΑ	4
Output high current (V _{OUT} = 1.420 V)	I _{OH}	-13.4	_	mA	_
Output low current (V _{OUT} = 0.280 V)	I _{OL}	13.4	—	mA	_

Table 13. DDR2 SDRAM DC Electrical Characteristics for GV_{DD}(typ) = 1.8 V

Notes:

1. ${\rm GV}_{\rm DD}$ is expected to be within 50 mV of the DRAM ${\rm GV}_{\rm DD}$ at all times.

2. MV_{REF} is expected to be equal to $0.5 \times GV_{DD}$, and to track GV_{DD} DC variations as measured at the receiver.

Peak-to-peak noise on MV_{REF} may not exceed ±2% of the DC value.

3. V_{TT} is not applied directly to the device. It is the supply to which far end signal termination is made and is expected to be equal to MV_{REF}. This rail should track variations in the DC level of MV_{REF}.

4. Output leakage is measured with all outputs disabled, 0 V \leq V_{OUT} \leq GV_{DD}.

This table provides the DDR2 capacitance when $GV_{DD}(typ) = 1.8$ V.

fable 14. DDR2	SDRAM	Capacitance	for	GV _{DD} (typ)=	=1.8 \
Table 14. DDR2	SDRAM	Capacitance	for	GV _{DD} (typ)=	=1.8 \

Parameter/Condition	Symbol	Min	Max	Unit	Notes
Input/output capacitance: DQ, DQS, DQS	C _{IO}	6	8	pF	1
Delta input/output capacitance: DQ, DQS, DQS	C _{DIO}	—	0.5	pF	1

Note:

1. This parameter is sampled. $GV_{DD} = 1.8 \text{ V} \pm 0.090 \text{ V}$, f = 1 MHz, T_A = 25°C, $V_{OUT} = GV_{DD}/2$, V_{OUT} (peak-to-peak) = 0.2 V.

This figure shows the MII receive AC timing diagram.



Figure 9. MII Receive AC Timing Diagram RMII AC Timing Specifications

This figure provides the AC test load.



Figure 10. AC Test Load

8.2.2 RGMII AC Timing Specifications

This table presents the RGMII AC timing specifications.

Table 25. RGMII AC Timing Specifications

At recommended operating conditions with LV_{DD} of 2.5 V \pm 5%.

Parameter/Condition	Symbol ¹	Min	Тур	Max	Unit
Data to clock output skew (at transmitter)	t _{SKRGT}	-0.6	—	0.6	ns
Data to clock input skew (at receiver) ²	t _{SKRGT}	1.0	—	2.6	ns
Clock cycle duration ³	t _{RGT}	7.2	8.0	8.8	ns
Duty cycle for 1000Base-T ^{4, 5}	t _{RGTH} /t _{RGT}	45	50	55	%
Duty cycle for 10BASE-T and 100BASE-TX ^{3, 5}	t _{RGTH} /t _{RGT}	40	50	60	%
Rise time (20%–80%)	t _{RGTR}	—	—	0.75	ns
Fall time (20%–80%)	t _{RGTF}	—	—	0.75	ns

and RGMII are specified in Section 8.1, "Enhanced Three-Speed Ethernet Controller (eTSEC) (10/100/1000 Mbps)—MII/RGMII Electrical Characteristics."

8.3.1 MII Management DC Electrical Characteristics

The MDC and MDIO are defined to operate at a supply voltage of 3.3 V. This table provides the DC electrical characteristics for MDIO and MDC.

Parameter	Symbol	Conditions		Min	Max	Unit
Supply voltage (3.3 V)	NV_{DD}	—		3.0	3.6	V
Output high voltage	V _{OH}	I _{OH} = -1.0 mA	NV _{DD} = Min	2.10	NV _{DD} + 0.3	V
Output low voltage	V _{OL}	l _{OL} = 1.0 mA	LV _{DD} = Min	VSS	0.50	V
Input high voltage	V _{IH}	_				V
Input low voltage	V _{IL}	_	_	—	0.80	V
Input high current	I _{IH}	NV _{DD} = Max	V _{IN} ¹ = 2.1 V	—	40	μΑ
Input low current	IIL	NV _{DD} = Max	V _{IN} = 0.5 V	-600	—	μΑ

Table 26. MII Management DC Electrical Characteristics When Powered at 3.3 V

Note:

1. V_{IN} , in this case, represents the LV_{IN} symbol referenced in Table 1 and Table 2.

8.3.2 MII Management AC Electrical Specifications

This table provides the MII management AC timing specifications.

Table 27. MII Management AC Timing Specifications

At recommended operating conditions with $\text{LV}_{\text{DDA}}/\text{LV}_{\text{DDB}}$ is 3.3 V \pm 0.3V

Parameter/Condition	Symbol ¹	Min	Тур	Мах	Unit	Notes
MDC frequency	f _{MDC}	_	2.5	—	MHz	2
MDC period	t _{MDC}	_	400	—	ns	—
MDC clock pulse width high	t _{MDCH}	32	—	—	ns	—
MDC to MDIO delay	t _{MDKHDX}	10	—	170	ns	3
MDIO to MDC setup time	t _{MDDVKH}	5	—	—	ns	—
MDIO to MDC hold time	t _{MDDXKH}	0	—	—	ns	—
MDC rise time	t _{MDCR}	—	—	10	ns	—

10 High-Speed Serial Interfaces (HSSI)

This section describes the common portion of SerDes DC electrical specifications, which is the DC requirement for SerDes reference clocks. The SerDes data lane's transmitter and receiver reference circuits are also shown.

10.1 Signal Terms Definition

The SerDes utilizes differential signaling to transfer data across the serial link. This section defines terms used in the description and specification of differential signals.

Figure 15 shows how the signals are defined. For illustration purpose, only one SerDes lane is used for description. The figure shows waveform for either a transmitter output $(TXn \text{ and } \overline{TXn})$ or a receiver input $(RXn \text{ and } \overline{RXn})$. Each signal swings between A Volts and B Volts where A > B.

Using this waveform, the definitions are as follows. To simplify illustration, the following definitions assume that the SerDes transmitter and receiver operate in a fully symmetrical differential signaling environment.

• Single-Ended Swing

The transmitter output signals and the receiver input signals TXn, \overline{TXn} , RXn, and \overline{RXn} each have a peak-to-peak swing of A – B Volts. This is also referred as each signal wire's single-ended swing.

Differential Output Voltage, V_{OD} (or Differential Output Swing)

The differential output voltage (or swing) of the transmitter, V_{OD} , is defined as the difference of the two complimentary output voltages: $V_{TXn} - V_{\overline{TXn}}$. The V_{OD} value can be either positive or negative.

• Differential Input Voltage, V_{ID} (or Differential Input Swing)

The differential input voltage (or swing) of the receiver, V_{ID} , is defined as the difference of the two complimentary input voltages: $V_{RXn} - V_{\overline{RXn}}$. The V_{ID} value can be either positive or negative.

Differential Peak Voltage, V_{DIFFp}

The peak value of the differential transmitter output signal or the differential receiver input signal is defined as Differential Peak Voltage, $V_{DIFFp} = |A - B|$ Volts.

• Differential Peak-to-Peak, VDIFFp-p

Since the differential output signal of the transmitter and the differential input signal of the receiver each range from A – B to –(A – B) Volts, the peak-to-peak value of the differential transmitter output signal or the differential receiver input signal is defined as differential peak-to-peak voltage, $V_{DIFFp-p} = 2*V_{DIFFp} = 2*|(A – B)|$ Volts, which is twice of differential swing in amplitude, or twice of the differential peak. For example, the output differential peak-peak voltage can also be calculated as $V_{TX-DIFFp-p} = 2*|V_{OD}|$.

• Differential Waveform

The differential waveform is constructed by subtracting the inverting signal (for example, \overline{TXn}) from the non-inverting signal (for example, TXn) within a differential pair. There is only one signal trace curve in a differential waveform. The voltage represented in the differential waveform is not referenced to ground. Refer to Figure 24 as an example for differential waveform.

10.2.1 SerDes Reference Clock Receiver Characteristics

Figure 16 shows a receiver reference diagram of the SerDes reference clocks.

- The supply voltage requirements for XCOREVDD are specified in Table 1 and Table 2.
- SerDes reference clock receiver reference circuit structure
 - The SD_REF_CLK and SD_REF_CLK are internally AC-coupled differential inputs as shown in Figure 16. Each differential clock input (SD_REF_CLK or SD_REF_CLK) has a 50-Ω termination to XCOREVSS followed by on-chip AC-coupling.
 - The external reference clock driver must be able to drive this termination.
 - The SerDes reference clock input can be either differential or single-ended. Refer to the Differential Mode and Single-ended Mode description below for further detailed requirements.
- The maximum average current requirement that also determines the common mode voltage range
 - When the SerDes reference clock differential inputs are DC coupled externally with the clock driver chip, the maximum average current allowed for each input pin is 8mA. In this case, the exact common mode input voltage is not critical as long as it is within the range allowed by the maximum average current of 8 mA (refer to the following bullet for more detail), since the input is AC-coupled on-chip.
 - This current limitation sets the maximum common mode input voltage to be less than 0.4 V (0.4 V/50 = 8 mA) while the minimum common mode input level is 0.1 V above XCOREVSS. For example, a clock with a 50/50 duty cycle can be produced by a clock driver with output driven by its current source from 0mA to 16mA (0–0.8 V), such that each phase of the differential input has a single-ended swing from 0 V to 800 mV with the common mode voltage at 400mV.
 - If the device driving the SD_REF_CLK and $\overline{SD_REF_CLK}$ inputs cannot drive 50 Ω to XCOREVSS DC, or it exceeds the maximum input current limitations, then it must be AC-coupled off-chip.
- The input amplitude requirement
 - This requirement is described in detail in the following sections.



Figure 16. Receiver of SerDes Reference Clocks



Figure 21. AC-Coupled Differential Connection with LVDS Clock Driver (Reference Only)

Figure 22 shows the SerDes reference clock connection reference circuits for LVPECL type clock driver. Since LVPECL driver's DC levels (both common mode voltages and output swing) are incompatible with MPC8308 SerDes reference clock input's DC requirement, AC-coupling has to be used.

This figure assumes that the LVPECL clock driver's output impedance is 50 Ω . R1 is used to DC-bias the LVPECL outputs prior to AC-coupling. Its value could be ranged from 140 Ω to 240 Ω depending on clock driver vendor's requirement. R2 is used together with the SerDes reference clock receiver's 50- Ω termination resistor to attenuate the LVPECL output's differential peak level such that it meets the MPC8308's SerDes reference clock's differential input amplitude requirement (between 200 mV and 800 mV differential peak). For example, if the LVPECL output's differential peak is 900 mV and the desired SerDes reference clock input amplitude is selected as 600 mV, the attenuation factor is 0.67, which requires R2 = 25 Ω . Please consult clock driver chip manufacturer to verify whether this connection scheme is compatible with a particular clock driver chip.



Figure 22. AC-Coupled Differential Connection with LVPECL Clock Driver (Reference Only)

High-Speed Serial Interfaces (HSSI)

This figure shows the SerDes reference clock connection reference circuits for a single-ended clock driver. It assumes the DC levels of the clock driver are compatible with the device's SerDes reference clock input's DC requirement.



Figure 23. Single-Ended Connection (Reference Only)

10.2.4 AC Requirements for SerDes Reference Clocks

The clock driver selected should provide a high quality reference clock with low phase noise and cycle-to-cycle jitter. Phase noise less than 100 kHz can be tracked by the PLL and data recovery loops and is less of a problem. Phase noise above 15 MHz is filtered by the PLL. The most problematic phase noise occurs in the 1–15 MHz range. The source impedance of the clock driver should be 50 Ω to match the transmission line and reduce reflections which are a source of noise to the system.

This table describes some AC parameters for PCI Express protocol.

Table 32. SerDes	Reference	Clock AC	Parameters
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At recommended operating conditions with XCOREVDD= $1.0V \pm 5\%$

Parameter	Symbol	Min	Max	Unit	Notes
Rising Edge Rate	Rise Edge Rate	1.0	4.0	V/ns	2, 3
Falling Edge Rate	Fall Edge Rate	1.0	4.0	V/ns	2, 3
Differential Input High Voltage	V _{IH}	+200	—	mV	2
Differential Input Low Voltage	V _{IL}	_	-200	mV	2

PCI Express

Parameter	Symbol	Comments	Min	Typical	Max	Units	Note
AC coupling capacitor	C _{TX}	All Transmitters shall be AC coupled. The AC coupling is required either within the media or within the transmitting component itself. An external capacitor of 100nF is recommended.	75		200	nF	_
Crosslink random timeout	T _{crosslink}	This random timeout helps resolve conflicts in crosslink configuration by eventually resulting in only one Downstream and one Upstream Port.	0	_	1	ms	7

Table 34. Differential Transmitter (TX) Output Specifications (continued)

Notes:

- 1. No test load is necessarily associated with this value.
- Specified at the measurement point into a timing and voltage compliance test load as shown in Figure 29 and measured over any 250 consecutive TX UIs. (Also refer to the transmitter compliance eye diagram shown in Figure 27.)
- 3. A T_{TX-EYE} = 0.70 UI provides for a total sum of deterministic and random jitter budget of T_{TX-JITTER-MAX} = 0.30 UI for the transmitter collected over any 250 consecutive TX UIs. The T_{TX-EYE-MEDIAN-to-MAX-JITTER} median is less than half of the total TX jitter budget collected over any 250 consecutive TX UIs. It should be noted that the median is not the same as the mean. The jitter median describes the point in time where the number of jitter points on either side is approximately equal as opposed to the averaged time value.
- 4. The transmitter input impedance shall result in a differential return loss greater than or equal to 12 dB and a common mode return loss greater than or equal to 6 dB over a frequency range of 50 MHz to 1.25 GHz. This input impedance requirement applies to all valid input levels. The reference impedance for return loss measurements is 50 Ω to ground for both the D+ and D– line (that is, as measured by a vector network analyzer with 50- Ω probes, see Figure 29). Note that the series capacitors, C_{TX}, is optional for the return loss measurement.
- 5. Measured between 20%–80% at transmitter package pins into a test load as shown in Figure 29 for both V_{TX-D+} and V_{TX-D-}.
- 6. See Section 4.3.1.8 of the PCI Express Base Specifications, Rev 1.0a.
- 7. See Section 4.2.6.3 of the PCI Express Base Specifications, Rev 1.0a.

11.4.2 Transmitter Compliance Eye Diagrams

The TX eye diagram in Figure 27 is specified using the passive compliance/test measurement load (Figure 29) in place of any real PCI Express interconnect + RX component. There are two eye diagrams that must be met for the transmitter. Both diagrams must be aligned in time using the jitter median to locate the center of the eye diagram. The different eye diagrams differ in voltage depending on whether it is a transition bit or a de-emphasized bit. The exact reduced voltage level of the de-emphasized bit is always relative to the transition bit.

The eye diagram must be valid for any 250 consecutive UIs.

A recovered TX UI is calculated over 3500 consecutive unit intervals of sample data. The eye diagram is created using all edges of the 250 consecutive UI in the center of the 3500 UI used for calculating the TX UI.

NOTE

It is recommended that the recovered TX UI be calculated using all edges in the 3500 consecutive UI interval with a fit algorithm using a minimization merit function (that is, least squares and median deviation fits).

Enhanced Local Bus

12.1 Enhanced Local Bus DC Electrical Characteristics

This table provides the DC electrical characteristics for the local bus interface.

Table 36. Local Bus DC Electrica	I Characteristics at 3.3 V
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Parameter	Symbol	Min	Max	Unit
High-level input voltage	V _{IH}	2.0	NV _{DD} + 0.3	V
Low-level input voltage	V _{IL}	-0.3	0.8	V
Input current, $(V_{IN}^{1} = 0 \text{ V or } V_{IN} = LV_{DD})$	I _{IN}	—	±5	μA
High-level output voltage, (LV _{DD} = min, $I_{OH} = -2$ mA)	V _{OH}	NV _{DD} – 0.2	—	V
Low-level output voltage, ($LV_{DD} = min$, $I_{OH} = 2 mA$)	V _{OL}	—	0.2	V

Note: The parameters stated in above table are valid for all revisions unless explicitly mentioned.

12.2 Enhanced Local Bus AC Electrical Specifications

This table describes the general timing parameters of the local bus interface.

Table 37. Local Bus General Timing Parameter	ers
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Parameter	Symbol ¹	Min	Max	Unit	Notes
Local bus cycle time	t _{LBK}	15	_	ns	2
Input setup to local bus clock	t _{LBIVKH}	7	_	ns	3, 4
Input hold from local bus clock	t _{LBIXKH}	1	_	ns	3, 4
Local bus clock to output valid	t _{LBKHOV}	—	3	ns	3
Local bus clock to output high impedance for LD	t _{LBKHOZ}	_	4	ns	5

Notes:

 The symbols used for timing specifications follow the pattern of t<sub>(First two letters of functional block)(signal)(state) (reference)(state) for inputs and t_{(First two letters of functional block)(reference)(state)(signal)(state)} for outputs. For example, t_{LBIXKH1} symbolizes local bus timing (LB) for the input (I) to go invalid (X) with respect to the time the t_{LBK} clock reference (K) goes high (H), in this case for clock one(1).
</sub>

 All timings are in reference to falling edge of LCLK0 (for all outputs and for LGTA and LUPWAIT inputs) or rising edge of LCLK0 (for all other inputs).

3. All signals are measured from NV_{DD}/2 of the rising/falling edge of LCLK0 to $0.4 \times NV_{DD}$ of the signal in question for 3.3-V signaling levels.

4. Input timings are measured at the pin.

5. For purposes of active/float timing measurements, the Hi-Z or off state is defined to be when the total current delivered through the component pin is less than or equal to the leakage current specification.

This figure provides the AC test load for the local bus.



Figure 30. Local Bus AC Test Load

Table 42. JTAG AC Timing Specifications (Independent of SYS_CLK_IN)¹ (continued)

At recommended operating conditions (see Table 2).

Parameter	Symbol ²	Min	Max	Unit	Note
Output hold times: Boundary-scan data TDO	t _{jtkldx} t _{jtklox}	2 2		ns	5
JTAG external clock to output high impedance: Boundary-scan data TDO	t _{jtkldz} t _{jtkloz}	2 2	19 9	ns	5, 6

Notes:

- 1. All outputs are measured from the midpoint voltage of the falling/rising edge of t_{TCLK} to the midpoint of the signal in question. The output timings are measured at the pins. All output timings assume a purely resistive 50- Ω load (see Figure 40). Time-of-flight delays must be added for trace lengths, vias, and connectors in the system.
- 2. The symbols used for timing specifications follow the pattern of t_{(first two letters of functional block)(signal)(state) (reference)(state) for inputs and t_{(first two letters of functional block)(reference)(state)(signal)(state) for outputs. For example, t_{JTDVKH} symbolizes JTAG device timing (JT) with respect to the time data input signals (D) reaching the valid state (V) relative to the t_{JTG} clock reference (K) going to the high (H) state or setup time. Also, t_{JTDXKH} symbolizes JTAG timing (JT) with respect to the time data input signals (D) went invalid (X) relative to the t_{JTG} clock reference (K) going to the high (H) state. Note that, in general, the clock reference symbol representation is based on three letters representing the clock of a particular functional. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).}}
- 3. TRST is an asynchronous level sensitive signal. The setup time is for test purposes only.
- 4. Non-JTAG signal input timing with respect to t_{TCLK}.
- 5. Non-JTAG signal output timing with respect to t_{TCLK}.
- 6. Guaranteed by design and characterization.

This figure provides the AC test load for TDO and the boundary-scan outputs.



Figure 40. AC Test Load for the JTAG Interface

This figure provides the JTAG clock input timing diagram.



VM = Midpoint Voltage (NV_{DD}/2)

Figure 41. JTAG Clock Input Timing Diagram

16 Timers

This section describes the DC and AC electrical specifications for the timers.

16.1 Timers DC Electrical Characteristics

This table provides the DC electrical characteristics for the MPC8308 timers pins, including TIN, TOUT, and TGATE.

Characteristic	Symbol	Condition	Min	Мах	Unit
Output high voltage	V _{OH}	I _{OH} = -8.0 mA	2.4	—	V
Output low voltage	V _{OL}	I _{OL} = 8.0 mA	—	0.5	V
Output low voltage	V _{OL}	I _{OL} = 3.2 mA	—	0.4	V
Input high voltage	V _{IH}	—	2.1	$NV_{DD} + 0.3$	V
Input low voltage	V _{IL}	—	-0.3	0.8	V
Input current	I _{IN}	$0~V \leq V_{IN} \leq NV_{DD}$	—	± 5	μΑ

Table 45. Timers DC Electrical Characteristics

16.2 Timers AC Timing Specifications

This table provides the timers input and output AC timing specifications.

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Table 46. Timers Input AC Timing Specifications
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Characteristic	Symbol ¹	Min	Unit
Timers inputs—minimum pulse width	t _{TIWID}	20	ns

Notes:

1. Timers inputs and outputs are asynchronous to any visible clock. Timers outputs should be synchronized before use by any external synchronous logic. Timers inputs are required to be valid for at least t_{TIWID} ns to ensure proper operation

This figure provides the AC test load for the Timers.



Figure 47. Timers AC Test Load

- 2. Dimensions and tolerances per ASME Y14.5M-1994.
- 3. Maximum solder ball diameter measured parallel to datum A.
- 4. Datum A, the seating plane, is determined by the spherical crowns of the solder balls.

20.3 Pinout Listings

This table provides the pin-out listing for the MPC8308, MAPBGA package.

Table 53. MPC8308 Pinout Listing

Signal	Pin Type	Power Supply	Note					
DDR Memory Controller Interface								
MEMC_MDQ[0]	V6	I/O	GV _{DDA}	—				
MEMC_MDQ[1]	Y4	I/O	GV _{DDA}	—				
MEMC_MDQ[2]	AB3	I/O	GV _{DDA}	—				
MEMC_MDQ[3]	AA3	I/O	GV _{DDA}	—				
MEMC_MDQ[4]	AA2	I/O	GV _{DDA}	—				
MEMC_MDQ[5]	AA1	I/O	GV _{DDA}	—				
MEMC_MDQ[6]	W4	I/O	GV _{DDA}	—				
MEMC_MDQ[7]	Y2	I/O	GV _{DDA}	—				
MEMC_MDQ[8]	W3	I/O	GV _{DDA}	—				
MEMC_MDQ[9]	W1	I/O	GV _{DDA}	—				
MEMC_MDQ[10]	Y1	I/O	GV _{DDA}	—				
MEMC_MDQ[11]	W2	I/O	GV _{DDA}	—				
MEMC_MDQ[12]	U4	I/O	GV _{DDA}	—				
MEMC_MDQ[13]	U3	I/O	GV _{DDA}	—				
MEMC_MDQ[14]	V4	I/O	GV _{DDA}	—				
MEMC_MDQ[15]	U6	I/O	GV _{DDA}	—				
MEMC_MDQ[16]	ТЗ	I/O	GV _{DDB}	—				
MEMC_MDQ[17]	T2	I/O	GV _{DDB}	—				
MEMC_MDQ[18]	R4	I/O	GV _{DDB}	_				
MEMC_MDQ[19]	R3	I/O	GV _{DDB}	—				
MEMC_MDQ[20]	P4	I/O	GV _{DDB}	—				
MEMC_MDQ[21]	N6	I/O	GV _{DDB}	—				
MEMC_MDQ[22]	P2	I/O	GV _{DDB}	_				
MEMC_MDQ[23]	P1	I/O	GV _{DDB}	—				
MEMC_MDQ[24]	N4	I/O	GV _{DDB}	-				
MEMC_MDQ[25]	N3	I/O	GV _{DDB}	-				
MEMC_MDQ[26]	N2	I/O	GV _{DDB}	—				

Package and Pin Listings

Signal	Package Pin Number	Pin Type	Power Supply	Note
MEMC_MCAS	C5	0	GV _{DDB}	-
MEMC_MCS[0]	B6	0	GV _{DDB}	<u> </u>
MEMC_MCS[1]	C6	0	GV _{DDB}	-
MEMC_MCKE	H3	0	GV _{DDB}	3
MEMC_MCK [0]	A3	0	GV _{DDB}	-
MEMC_MCK [1]	U2	0	GV _{DDB}	-
MEMC_MCK [2]	G1	0	GV _{DDB}	-
MEMC_MCK [0]	A4	0	GV _{DDB}	—
MEMC_MCK [1]	U1	0	GV _{DDB}	-
MEMC_MCK [2]	H1	0	GV _{DDB}	-
MEMC_MODT[0]	A5	0	GV _{DDB}	—
MEMC_MODT[1]	B5	0	GV _{DDB}	—
MEMC_MECC[0]	L4	I/O	GV _{DDB}	-
MEMC_MECC[1]	L6	I/O	GV _{DDB}	—
MEMC_MECC[2]	K4	I/O	GV _{DDB}	—
MEMC_MECC[3]	КЗ	I/O	GV _{DDB}	—
MEMC_MECC[4]	J2	I/O	GV _{DDB}	—
MEMC_MECC[5]	К6	I/O	GV _{DDB}	—
MEMC_MECC[6]	J3	I/O	GV _{DDB}	—
MEMC_MECC[7]	J6	I/O	GV _{DDB}	—
MV _{REF}	G6	I	GV _{DDB}	—
	Local Bus Controller Interface			
LD0	U18	I/O	NV_{DDP_K}	8
LD1	V18	I/O	NV_{DDP_K}	8
LD2	U16	I/O	NV_{DDP_K}	8
LD3	Y20	I/O	NV_{DDP_K}	8
LD4	AA21	I/O	NV_{DDP_K}	8
LD5	AC22	I/O	NV_{DDP_K}	8
LD6	V17	I/O	NV _{DDP_K}	8
LD7	AB21	I/O	NV _{DDP_K}	8
LD8	Y19	I/O	NV _{DDP_K}	8
LD9	AA20	I/O	NV _{DDP_K}	8
LD10	Y17	I/O	NV _{DDP_K}	8

Table 53. MPC8308 Pinout Listing (continued)

Package and Pin Listings

Table 53. M	PC8308 Pinou	Listing	(continued)
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Signal	Package Pin Number	Pin Type	Power Supply	Note
LCS[3]	Y11	0	NV _{DDP_K}	4
LWE[0] /LFWE0/LBS0	AB11	0	NV _{DDP_K}	
LWE[1]/LBS1	AC11	0	NV _{DDP_K}	
LBCTL	U11	0	NV _{DDP_K}	
LGPL0/LFCLE	Y10	0	NV _{DDP_K}	
LGPL1/LFALE	AA10	0	NV _{DDP_K}	
LGPL2/LOE/LFRE	AB10	0	NV _{DDP_K}	4
LGPL3/LFWP	AC10	0	NV _{DDP_K}	
LGPL4/ LGTA /LUPWAIT/ LFRB	AB9	I/O	NV _{DDP_K}	4
LGPL5	Y9	0	NV _{DDP_K}	
LCLK0	AC12	0	NV _{DDP_K}	
	DUART		I	1
UART_SOUT1/MSRCID0/ LSRCID0	C17	0	NV _{DDB}	—
UART_SIN1/MSRCID1/ LSRCID1	B18	I/O	NV _{DDB}	—
UART_SOUT2/MSRCID2/ LSRCID2	D17	0	NV _{DDB}	-
UART_SIN2/MSRCID3/ LSRCID3	D18	I/O	NV _{DDB}	—
	PEX PHY			I
ТХА	C14	0	XPADVDD	
TXA	C15	0	XPADVDD	
RXA	A13	I	XCOREVDD	
RXA	B13	I	XCOREVDD	
SD_IMP_CAL_RX	A15	I	XCOREVDD	
SD_REF_CLK	C12	I	XCOREVDD	—
SD_REF_CLK	D12	I	XCOREVDD	—
SD_PLL_TPD	F13	0	—	—
SD_IMP_CAL_TX	A11	I	XPADVDD	—
SD_PLL_TPA_ANA	F11	0	—	—
SDAVDD_0	G12	I	—	—
SDAVSS_0	F12	I	—	—
	I ² C interface		•	
IIC_SDA1	C9	I/O	NV _{DDA}	2

21 Clocking

This figure shows the internal distribution of clocks within the device.



¹ Multiplication factor M = 1, 1.5, 2, 2.5, and 3. Value is decided by RCWLR[COREPLL].

 2 Multiplication factor L = 2, 3, 4, 5 and 6. Value is decided by RCWLR[SPMF].

Figure 53. MPC8308 Clock Subsystem

The following external clock sources are utilized on the MPC8308:

- System clock (SYS_CLK_IN)
- Ethernet Clock (TSEC1_RX_CLK/TSEC1_TX_CLK/TSEC1_GTX_CLK125 for eTSEC)
- SerDes PHY clock
- eSHDC clock (SD_CLK)

For more information, see the SerDes chapter in the *MPC8308 PowerQUICC II Pro Processor Reference Manual.*

All clock inputs can be supplied using an external canned oscillator, a clock generation chip, or some other source that provides a standard CMOS square wave input.

Thermal

appropriate for a tightly packed printed-circuit board. The value obtained on the board with the internal planes is usually appropriate if the board has low power dissipation and the components are well separated. Test cases have demonstrated that errors of a factor of two (in the quantity $T_J - T_A$) are possible.

22.2.2 Estimation of Junction Temperature with Junction-to-Board Thermal Resistance

The thermal performance of a device cannot be adequately predicted from the junction-to-ambient thermal resistance. The thermal performance of any component is strongly dependent on the power dissipation of surrounding components. In addition, the ambient temperature varies widely within the application. For many natural convection and especially closed box applications, the board temperature at the perimeter (edge) of the package is approximately the same as the local air temperature near the device. Specifying the local ambient conditions explicitly as the board temperature provides a more precise description of the local ambient conditions that determine the temperature of the device.

At a known board temperature, the junction temperature is estimated using the following equation:

$$T_J = T_B + (R_{\theta JB} \times P_D)$$

where:

 T_I = junction temperature (°C)

 T_B = board temperature at the package perimeter (°C)

 $R_{\theta JB}$ = junction-to-board thermal resistance (°C/W) per JESD51–8

 P_D = power dissipation in the package (W)

When the heat loss from the package case to the air can be ignored, acceptable predictions of junction temperature can be made. The application board should be similar to the thermal test condition: the component is soldered to a board with internal planes.

22.2.3 Experimental Determination of Junction Temperature

To determine the junction temperature of the device in the application after prototypes are available, the thermal characterization parameter (Ψ_{JT}) can be used to determine the junction temperature with a measurement of the temperature at the top center of the package case using the following equation:

$$T_J = T_T + (\Psi_{JT} \times P_D)$$

where:

 T_J = junction temperature (°C) T_T = thermocouple temperature on top of package (°C) Ψ_{JT} = thermal characterization parameter (°C/W)

 P_D = power dissipation in the package (W)

The thermal characterization parameter is measured per JESD51-2 specification using a 40 gauge type T thermocouple epoxied to the top center of the package case. The thermocouple should be positioned so that the thermocouple junction rests on the package. A small amount of epoxy is placed over the thermocouple junction and over about 1 mm of wire extending from the junction. The thermocouple wire is placed flat against the package case to avoid measurement errors caused by cooling effects of the thermocouple wire.

System Design Information

23 System Design Information

This section provides electrical and thermal design recommendations for successful application of the device

23.1 System Clocking

The device includes two PLLs.

- 1. The platform PLL generates the platform clock from the externally supplied SYS_CLK_IN input. The frequency ratio between the platform and SYS_CLK_IN is selected using the platform PLL ratio configuration bits as described in Section 21.2, "System PLL Configuration."
- 2. The e300 core PLL generates the core clock as a slave to the platform clock. The frequency ratio between the e300 core clock and the platform clock is selected using the e300 PLL ratio configuration bits as described in Section 21.3, "Core PLL Configuration."

23.2 PLL Power Supply Filtering

Each of the PLLs listed above is provided with power through independent power supply pins (AV_{DD1} for core PLL and AV_{DD2} for the platform PLL). The AV_{DD} level should always be equivalent to V_{DD} , and preferably these voltages are derived directly from V_{DD} through a low pass filter scheme such as the following.

There are a number of ways to reliably provide power to the PLLs, but the recommended solution is to provide independent filter circuits as illustrated in Figure 54, one to each of the two AV_{DD} pins. By providing independent filters to each PLL the opportunity to cause noise injection from one PLL to the other is reduced.

This circuit is intended to filter noise in the PLLs' resonant frequency range from a 500 kHz to 10 MHz range. It should be built with surface mount capacitors with minimum effective series inductance (ESL). Consistent with the recommendations of Dr. Howard Johnson in *High Speed Digital Design: A Handbook of Black Magic* (Prentice Hall, 1993), multiple small capacitors of equal value are recommended over a single large value capacitor.

Each circuit should be placed as close as possible to the specific AV_{DD} pin being supplied to minimize noise coupled from nearby circuits. It should be possible to route directly from the capacitors to the AV_{DD} pin, which is on the periphery of package, without the inductance of vias.

This figure shows the PLL power supply filter circuits.



Figure 54. PLL Power Supply Filter Circuit

23.3 Decoupling Recommendations

Due to large address and data buses, and high operating frequencies, the device can generate transient power surges and high frequency noise in its power supply, especially while driving large capacitive loads. This noise must be prevented from reaching other components in the MPC8308 system, and the MPC8308 itself requires a clean, tightly regulated source of power. Therefore, it is recommended that the system designer place at least one decoupling capacitor at each V_{DD} , NV_{DD} , GV_{DD} and LV_{DD} pin of the device. These decoupling capacitors should receive their power from separate V_{DD} , NV_{DD} , GV_{DD} , LV_{DD} , and V_{SS} power planes in the PCB, utilizing short traces to minimize inductance. Capacitors may be placed directly under the device using a standard escape pattern. Others may surround the part.

These capacitors should have a value of 0.01 or 0.1 μ F. Only ceramic SMT (surface mount technology) capacitors should be used to minimize lead inductance, preferably 0402 or 0603 sizes.

In addition, it is recommended that there be several bulk storage capacitors distributed around the PCB, feeding the V_{DD} , NV_{DD} , GV_{DD} , LV_{DD} planes, to enable quick recharging of the smaller chip capacitors. These bulk capacitors should have a low ESR (equivalent series resistance) rating to ensure the quick response time necessary. They should also be connected to the power and ground planes through two vias to minimize inductance. Suggested bulk capacitors—100 to 330 μ F (AVX TPS tantalum or Sanyo OSCON). However, customers should work directly with their power regulator vendor for best values and types of bulk capacitors.

23.4 Connection Recommendations

To ensure reliable operation, it is highly recommended to connect unused inputs to an appropriate signal level. Unused active low inputs should be tied to NV_{DD} , GV_{DD} , LV_{DD} as required. Unused active high inputs should be connected to VSS. All NC (no-connect) signals must remain unconnected.

Power and ground connections must be made to all external V_{DD} , NV_{DD} , AV_{DD1} , AV_{DD2} , GV_{DD} , LV_{DD} and V_{SS} pins of the device.

23.5 Output Buffer DC Impedance

The device drivers are characterized over process, voltage, and temperature. For all buses, the driver is a push-pull single-ended driver type (open drain for I²C, MDIO and HRESET)

To measure Z_0 for the single-ended drivers, an external resistor is connected from the chip pad to NV_{DD} or V_{SS} . Then, the value of each resistor is varied until the pad voltage is $NV_{DD}/2$ (Figure 55). The output impedance is the average of two components, the resistances of the pull-up and pull-down devices. When data is held high, SW1 is closed (SW2 is open), and R_P is trimmed until the voltage at the pad equals $NV_{DD}/2$. R_P then becomes the resistance of the pull-up devices. R_P and R_N are designed to be close to each other in value. Then, $Z_0 = (R_P + R_N)/2$.

23.7 Pull-Up Resistor Requirements

The device requires high resistance pull-up resistors (10 k Ω is recommended) on open drain type pins including I²C, Ethernet management MDIO, HRESET and IPIC (integrated programmable interrupt controller).

Correct operation of the JTAG interface requires configuration of a group of system control pins as demonstrated in Figure 56. Care must be taken to ensure that these pins are maintained at a valid deasserted state under normal operating conditions because most have asynchronous behavior and spurious assertion, which give unpredictable results.

24 Ordering Information

This section presents ordering information for the devices discussed in this document, and it shows an example of how the parts are marked. Ordering information for the devices fully covered by this document is provided in Section 24.1, "Part Numbers Fully Addressed by This Document."

24.1 Part Numbers Fully Addressed by This Document

This table provides the Freescale part numbering nomenclature for the MPC8308 family. Note that the individual part numbers correspond to a maximum processor core frequency. For available frequencies, contact your local Freescale sales office. In addition to the maximum processor core frequency, the part numbering scheme also includes the maximum effective DDR memory speed. Each part number also contains a revision code which refers to the die mask revision number.

MPC	nnnn	С	VM	AD	D	Α
Product Code	Part Identifier	Temperature Range ^{1,4}	Package ²	e300 Core Frequency ³	DDR Frequency	Revision Level
MPC	8308	Blank = 0 to 105°C C = -40 to 105°C	VM = Pb-free 473 MAPBGA	AD = 266 MHz AF = 333 MHz AG = 400 MHz	D = 266 MHz	Contact local Freescale sales office

Table 61. Part Numbering Nomenclature

Notes:

1. Contact local Freescale office on availability of parts with C temperature range.

2. See Section 20, "Package and Pin Listings," for more information on available package types.

3. Processor core frequencies supported by parts addressed by this specification only. Not all parts described in this specification support all core frequencies. Additionally, parts addressed by Part Number Specifications may support other maximum core frequencies

4. Minimum temperature is specified with T_A ; Maximum temperature is specified with T_J